

1 ABSTRACT OF THE DISCLOSURE

2 A method of forming a capacitor includes, a) providing a node  
3 to which electrical connection to a first capacitor plate is to be made;  
4 b) then, providing a finned lower capacitor plate in ohmic electrical  
5 connection with the node using no more than one photomasking step;  
6 and c) providing a capacitor dielectric layer and a conductive second  
7 capacitor plate layer over the conductive layer. Such is preferably  
8 accomplished by, i) providing a layer of conductive material outwardly  
9 of the node; ii) providing a first masking layer over the conductive  
10 material layer; iii) etching a first opening into the first masking layer  
11 over the node; iv) providing a second masking layer over the first  
12 masking layer to a thickness which less than completely fills the first  
13 opening; v) anisotropically etching the second masking layer to define  
14 a spacer received laterally within the first opening and thereby defining  
15 a second opening relative to the first masking layer which is smaller  
16 than the first opening; vi) after said anisotropically etching, etching  
17 unmasked first masking layer material away; vii) after said  
18 anisotropically etching, etching through the conductive material layer to  
19 extend the second opening to the node, the node and conductive layer  
20 being electrically isolated from one another after the conductive material  
21 layer etching; viii) plugging the extended second opening with an  
22 electrically conductive plugging material, the plugging material electrically  
23 interconnecting the node and conductive layer. Novel capacitor  
24 constructions are also disclosed.